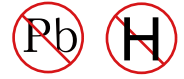




YEA SHIN TECHNOLOGY CO., LTD

YS3912ZBB

N-Channel Enhancement MOSFET



VDS= 30V, ID= 25A

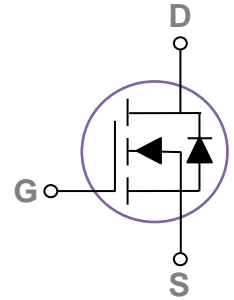
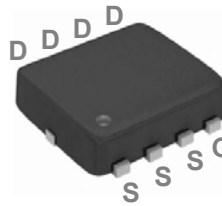
Features

- 30V,25A, $R_{DS(ON)} = 18m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- MB / VGA / Vcore
- POL Buck Applications
- SMPS 2nd SR

PPAK3x3 Pin Configuration



Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous ($T_c=25^\circ C$)	25	A
	Drain Current – Continuous ($T_c=100^\circ C$)	16	A
I _{DM}	Drain Current – Pulsed ¹	100	A
EAS	Single Pulse Avalanche Energy ²	32	mJ
IAS	Single Pulse Avalanche Current ²	8	A
P _D	Power Dissipation ($T_c=25^\circ C$)	21	W
	Power Dissipation – Derate above 25 ^o C	0.17	W/ ^o C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	62	°C /W
R _{θJC}	Thermal Resistance Junction to Case	---	6	°C /W

DEVICE CHARACTERISTICS

YS3912ZBB

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.04	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-source On-Resistance ³	$V_{GS}=10V, I_D=12A$	---	14	18	$m\Omega$
		$V_{GS}=4.5V, I_D=8A$	---	20	28	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	$mV/^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=6A$	---	6.5	---	S

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{3,4}	$V_{DS}=15V, V_{GS}=4.5V, I_D=6A$	---	4.1	8	nC
Q_{gs}	Gate-Source Charge ^{3,4}		---	1	2	
Q_{gd}	Gate-Drain Charge ^{3,4}		---	2.1	4	
$T_{d(on)}$	Turn-On Delay Time ^{3,4}	$V_{DD}=15V, V_{GS}=10V, R_G=6\Omega, I_D=1A$	---	2.8	5	ns
T_r	Rise Time ^{3,4}		---	7.2	14	
$T_{d(off)}$	Turn-Off Delay Time ^{3,4}		---	15.8	30	
T_f	Fall Time ^{3,4}		---	4.6	9	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	---	345	500	pF
C_{oss}	Output Capacitance		---	55	80	
C_{rss}	Reverse Transfer Capacitance		---	32	45	
R_g	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	---	3.2	6.4	Ω

Drain-Source Diode Characteristics and Maximum Ratings

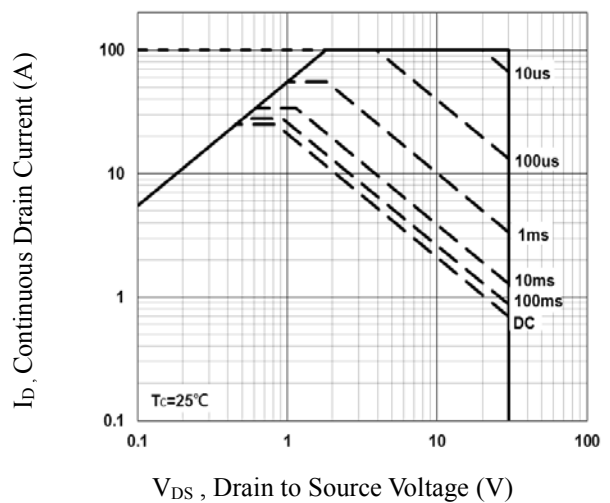
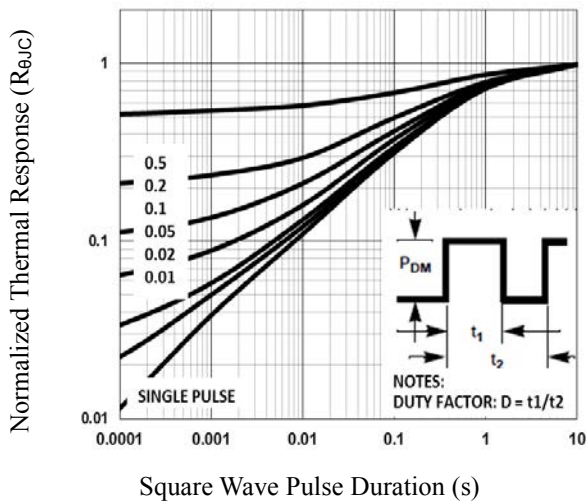
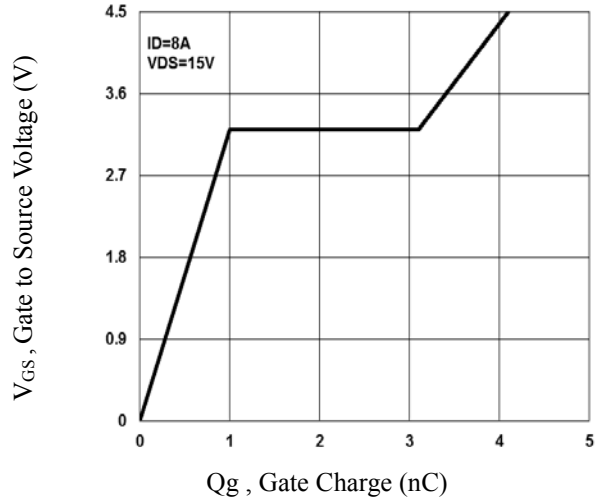
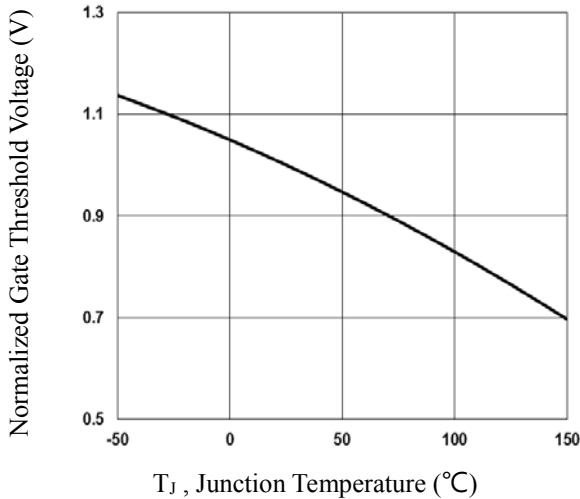
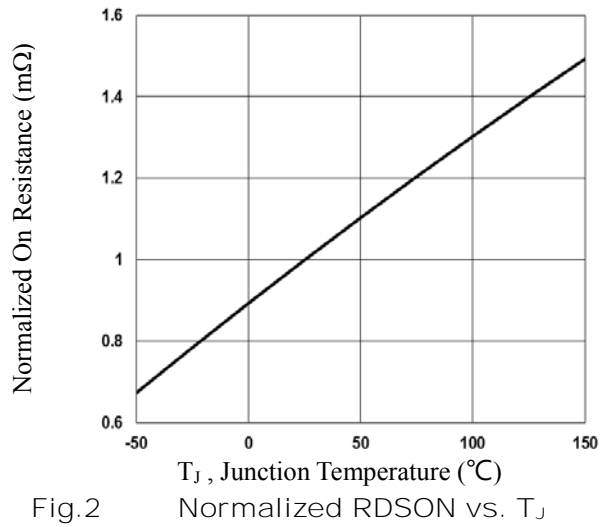
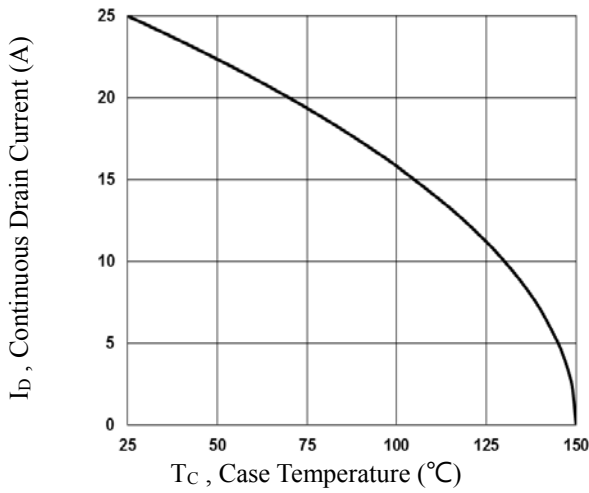
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	25	A
I_{SM}	Pulsed Source Current ³		---	---	50	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	0.7	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=8A, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

DEVICE CHARACTERISTICS

YS3912ZBB



DEVICE CHARACTERISTICS

YS3912ZBB

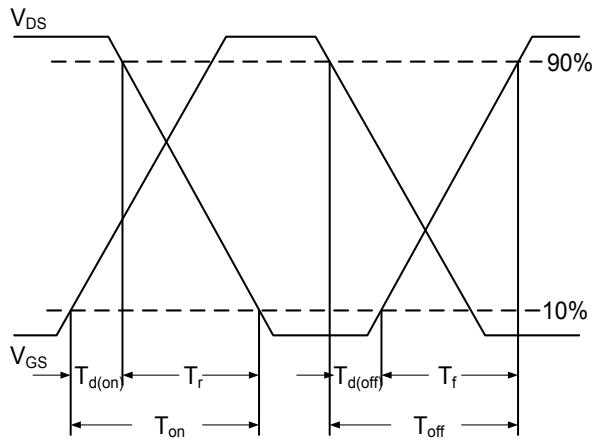


Fig.7 Switching Time Waveform

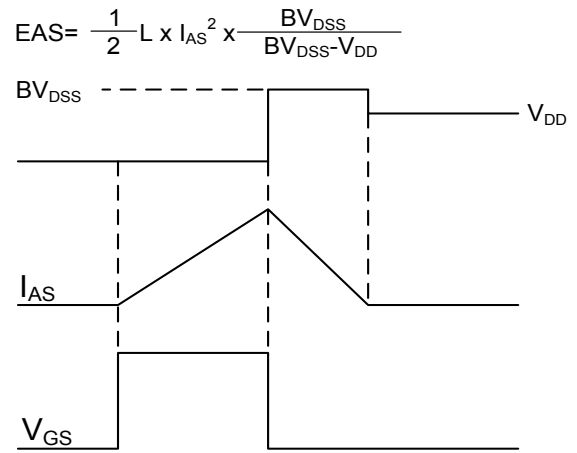
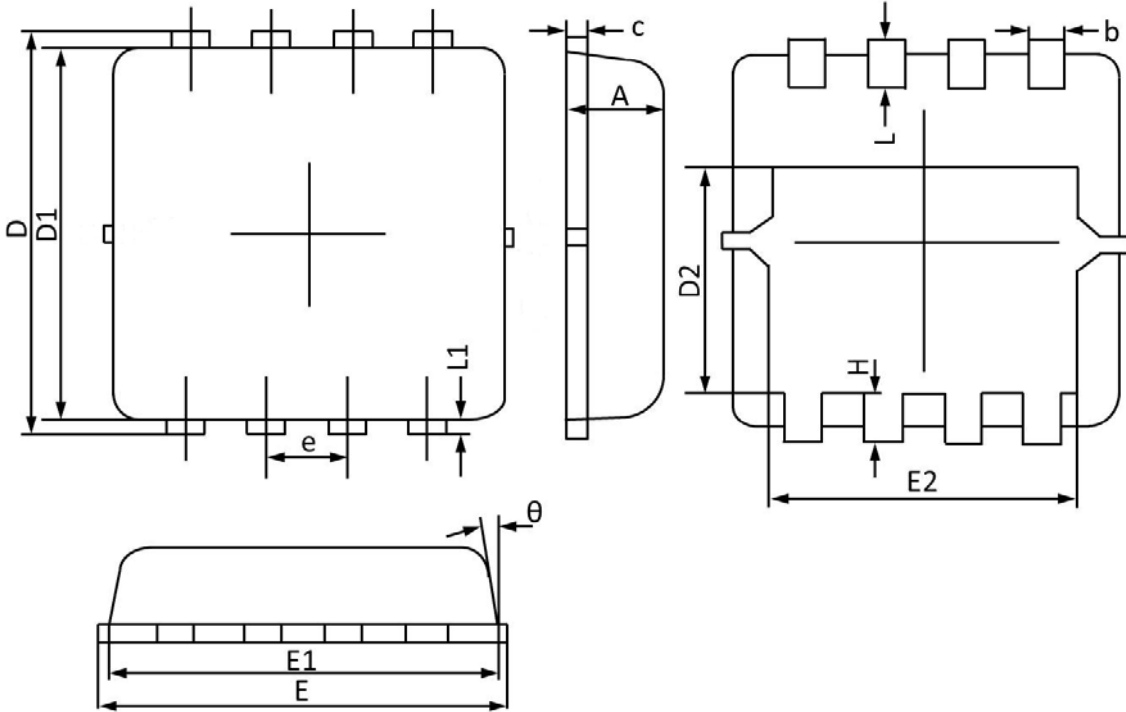


Fig.8 EAS Waveform

PACKAGE OUTLINE & DIMENSIONS

YS3912ZBB

PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
b	0.240	0.350	0.009	0.014
c	0.100	0.250	0.004	0.010
D	3.050	3.450	0.120	0.136
D1	2.900	3.200	0.114	0.126
D2	1.350	1.850	0.053	0.073
E	3.000	3.400	0.118	0.134
E1	2.900	3.250	0.114	0.128
E2	2.350	2.600	0.093	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.012	0.020
L	0.300	0.500	0.012	0.020
L1	0.070	0.200	0.003	0.008
θ	0°	12°	0°	12°